

# A Multifunctional Coating on Sulfur-containing Carbon-based Anode for High-performance Sodium-ion Batteries

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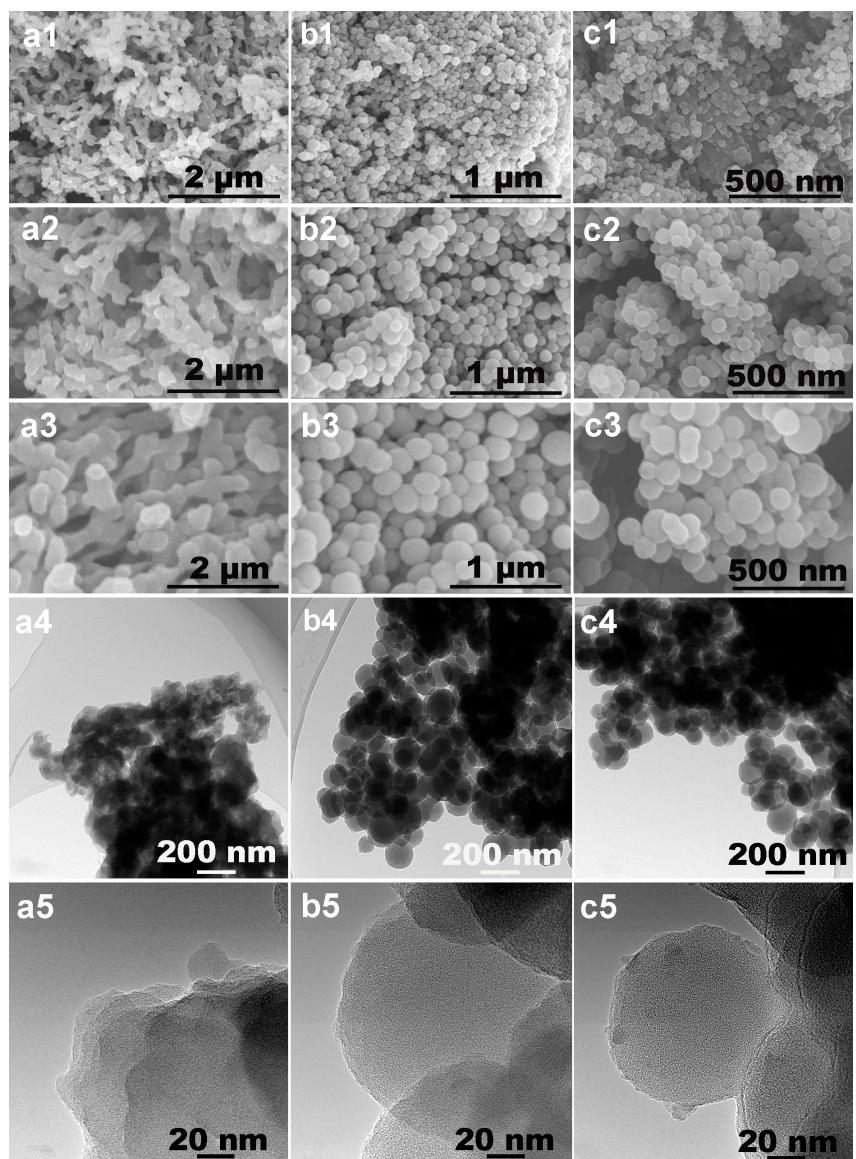
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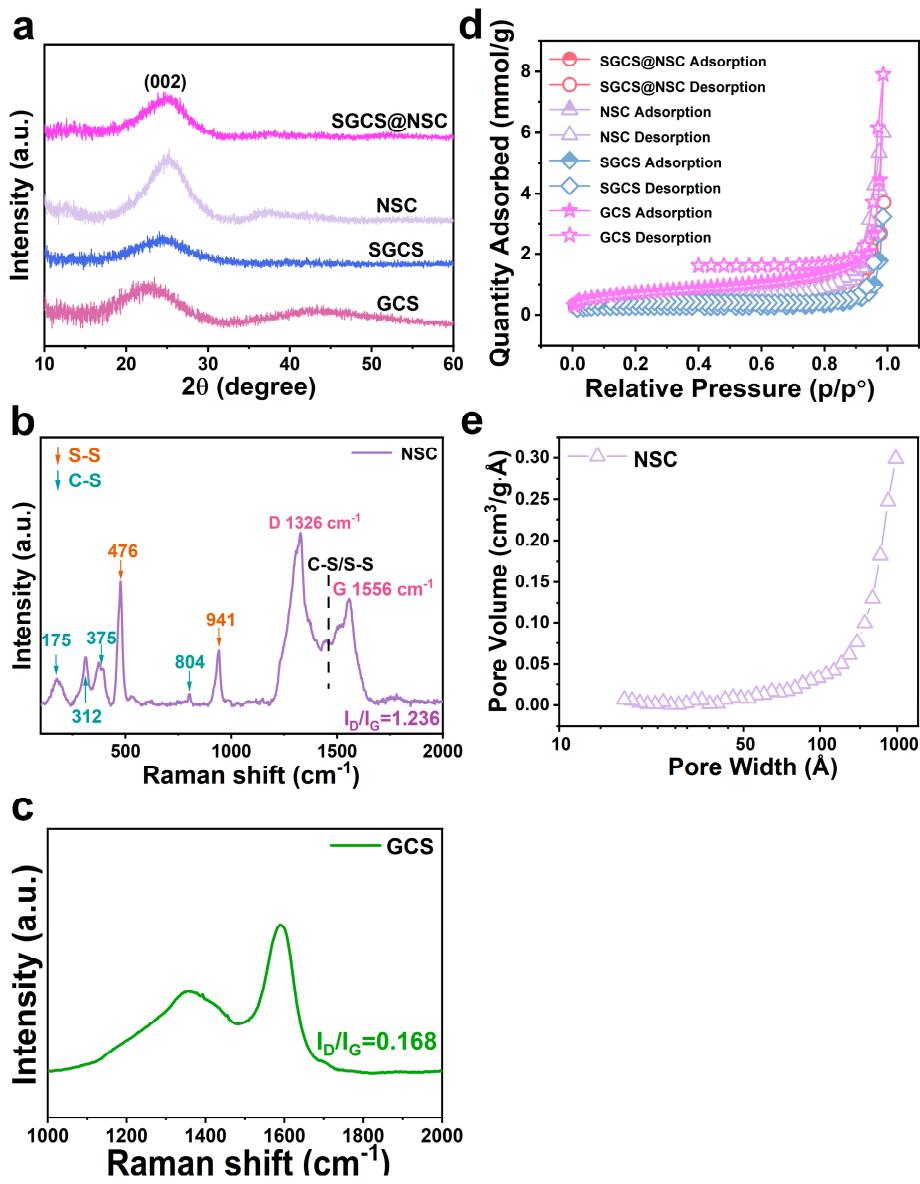
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**Table S1.** Summary of some different carbon-based materials for SIBs

Number	Material	Reversible capacity (mAh g <sup>-1</sup> , at A g <sup>-1</sup> )	ICE (%)	Reference
1	G-NCs	329 (0.05 A g <sup>-1</sup> )	32	Ref. [51]
2	Natural graphite	127 (0.1 A g <sup>-1</sup> )	-	Ref.[52]
3	A-CG	280 (0.04 A g <sup>-1</sup> )	38	Ref. [53]
4	HPCCNFs-1	215 (0.1 A g <sup>-1</sup> )	25.3	Ref.[15]
5	P-CNSs	237.5 (0.05 A g <sup>-1</sup> )	42.65	Ref.[37]
6	HCS-1900	295 (0.05 A g <sup>-1</sup> )	68.8	Ref. [54]
7	SNMHCSs	240 (0.05 A g <sup>-1</sup> )	29	Ref. [55]
8	PC-800	263.2 (0.05 A g <sup>-1</sup> )	79.6	Ref. [56]



**Figure S1.** The SEM images of **a1, a2, a3**) NSC, **b1, b2, b3**) SGCS and **c1, c2, c3**) GCS at different magnifications. TEM and HRTEM images of **a4, a5**) NSC, **b4, b5**) SGCS and **c4, c5**) GCS.



**Figure S2.** (a) X-ray diffraction patterns of SGCS@NSC, NSC, SGCS, and GCS. (b, c) Raman scattering spectra of NSC and GCS. (d) N2 adsorption-desorption isotherms of SGCS@NSC, NSC, SGCS, and GCS. (e) Pore distribution curves of NSC.

**Table S2.** Analysis of sulfur bonding area ratio of SGCS@NSC and SGCS.

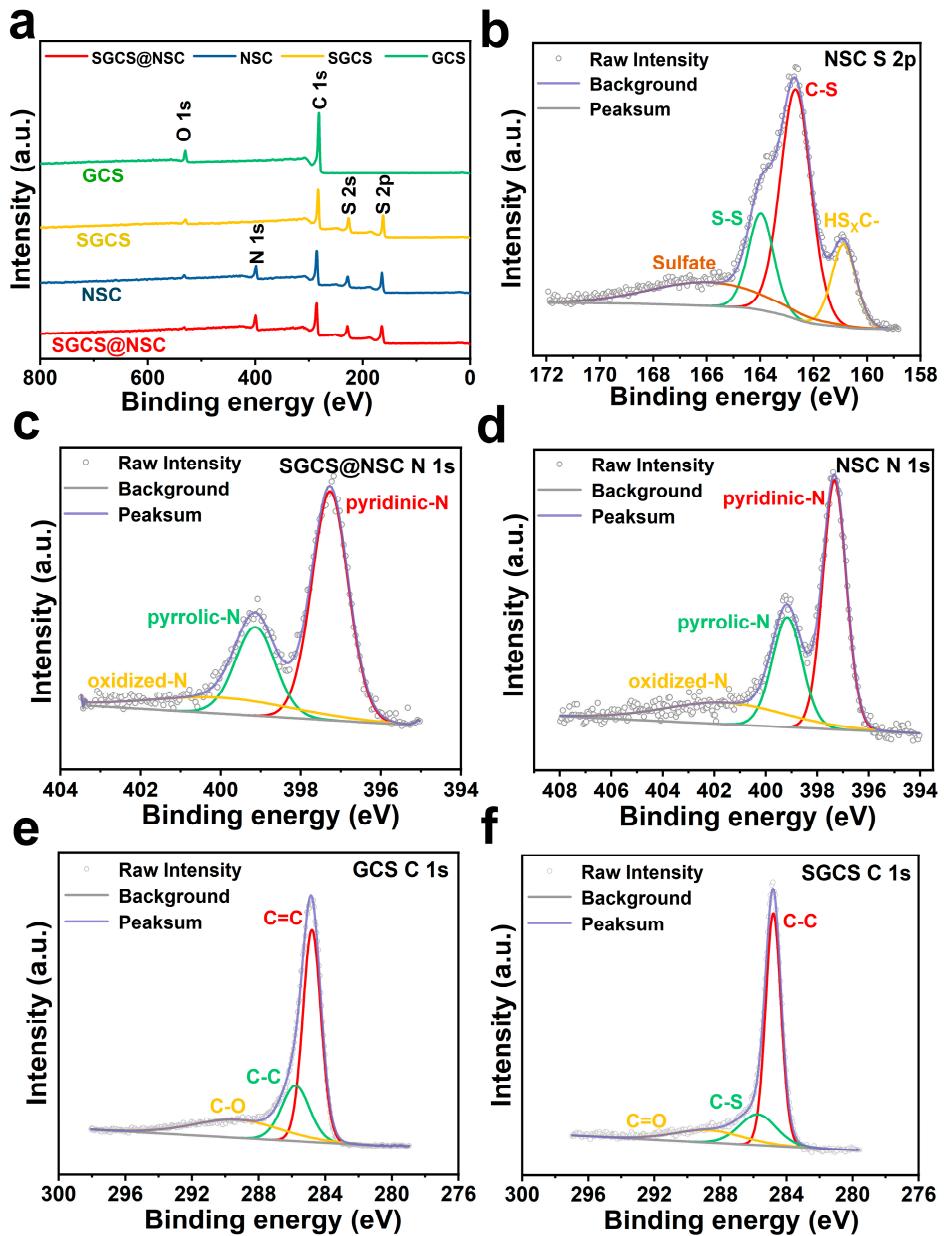
Sulfur bonding	SGCS@NSC	SGCS
HSxC-	8.1	
C-S	70.3	54.5
S-S	11.3	29.1
Sulfate	10.3	16.3

**Table S3.** Analysis of carbon bonding area ratio of SGCS@NSC and SGCS.

Carbon bonding	SGCS@NSC	SGCS
C-C	35.9	36.3
C-N/C-S	18.0	12.5
C=O/C=N	46.0	51.2

**Table S4.** Specific surface areas and pore volume analysis of SGCS@NSC, SGCS, GCS, and NSC.

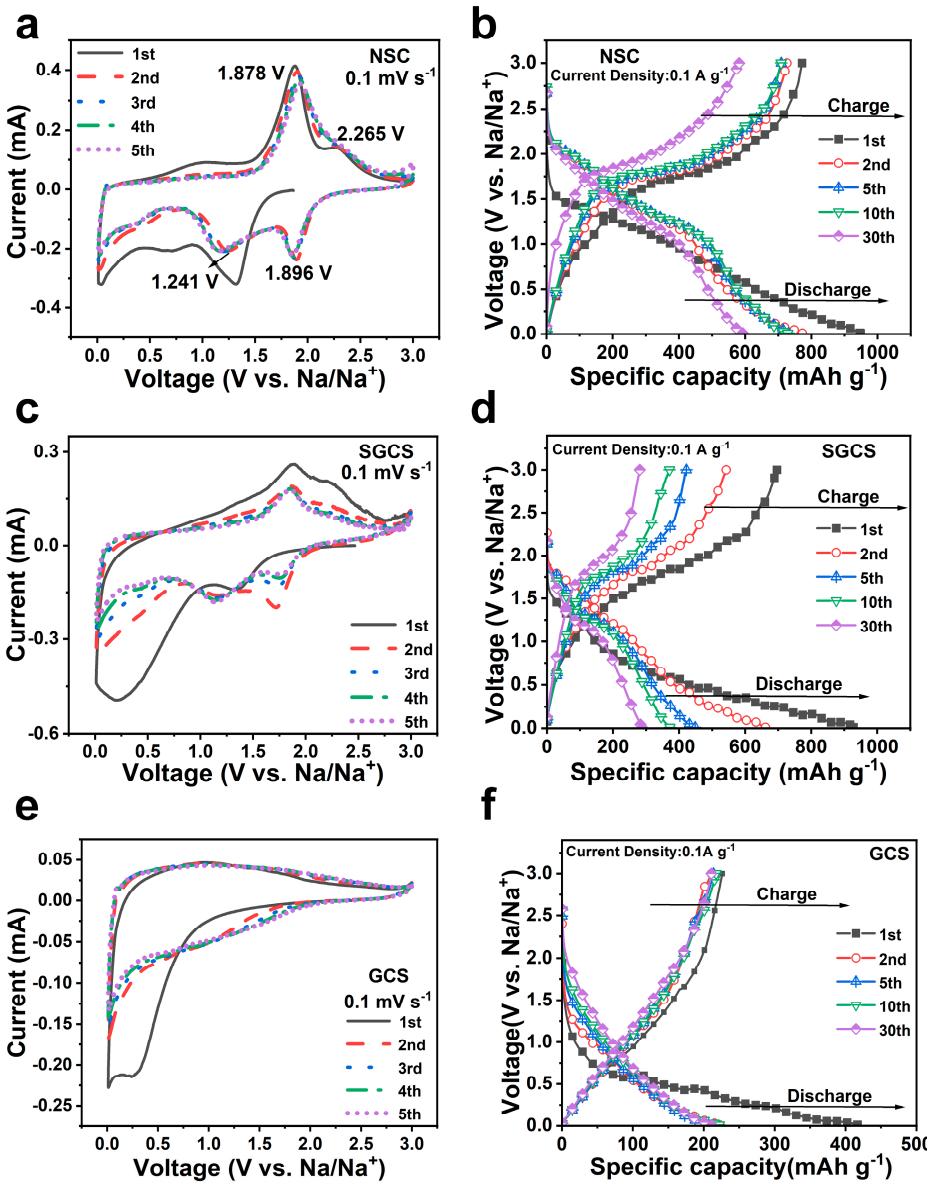
Samples	$S_{BET}(\text{m}^2/\text{g})$	$V_{\text{pore}}(\text{cm}^3/\text{g})$	$R_{\text{pore}}(\text{nm})$
<b>SGCS@NSC</b>	34.956	0.128	3.683
<b>SGCS</b>	18.670	0.113	6.052
<b>GCS</b>	56.147	0.274	4.880
<b>NSC</b>	31.168	0.208	8.984



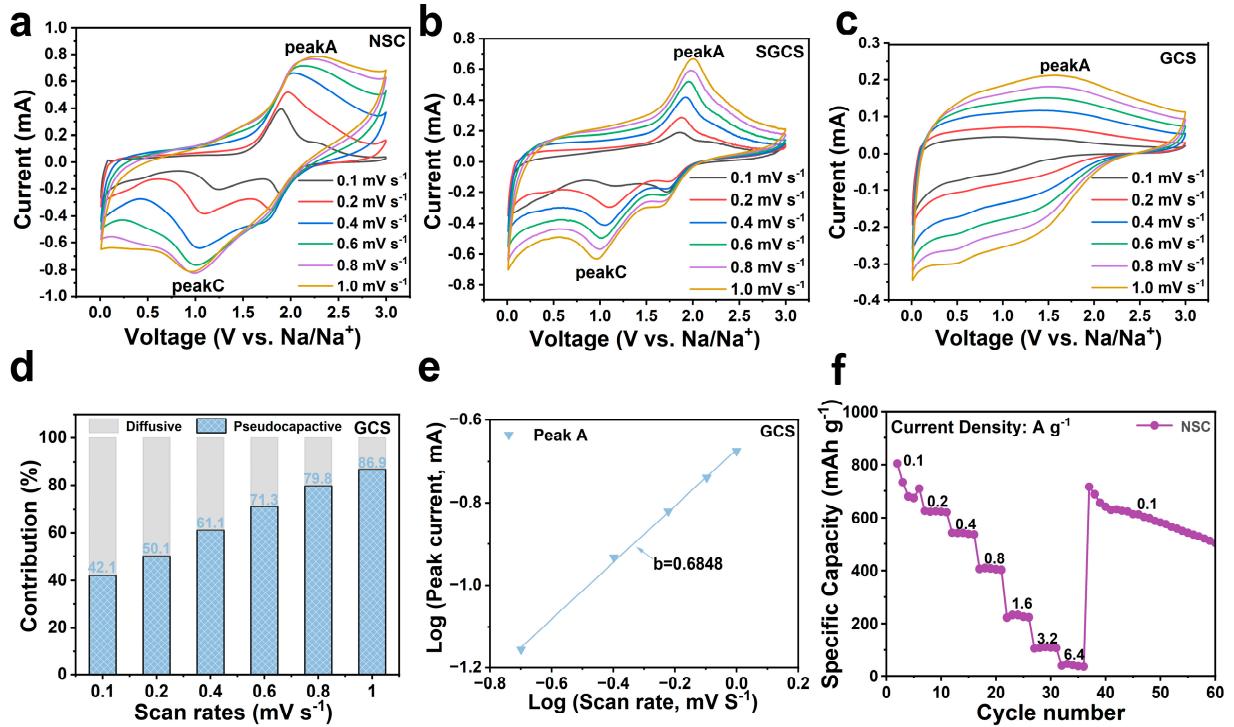
**Figure S3.** (a) Typical XPS survey spectra. (b, d, f) The high-resolution XPS of S 2p, N 1s, and C 1s for NSC, respectively. (c) The high-resolution XPS of N 1s for SGCS@NSC. (e) The high-resolution XPS of C 1s for GCS

**Table S5.** Element composition and ratio of the surface of four groups of samples calculated from XPS data (wt.%).

Samples	C (at%)	N (at%)	S (at%)	O (at%)
SGCS@NSC	63.019	12.637	19.075	2.471
NSC	61.019	16.542	19.860	1.813
SGCS	71.471		22.083	5.446
GCS	92.808			7.192



**Figure S4.** The first five successive CV curves of **a**) NSC, **c**) SGCS, and **e**) GCS at the scan rate of  $0.1 \text{ mV s}^{-1}$ . Galvanostatic discharge-charge profiles ( $100 \text{ mA g}^{-1}$ ) at the  $1^{\text{st}}$ ,  $2^{\text{nd}}$ ,  $5^{\text{th}}$ ,  $10^{\text{th}}$ , and  $30^{\text{th}}$  cycles of **b**) NSC, **d**) SGCS, and **f**) GCS.



**Figure S5.** CV curves at different scan rates of a) NSC, b) SGCS, and c) GCS from 0.1 to 1.0 mV s<sup>-1</sup>. (d) Normalized pseudocapacitive contribution ratios of GCS at scan rates from 0.1 to 1.0 mV s<sup>-1</sup>. (e) Log ( $i$ ) versus log ( $v$ ) plots of GCS at selected peak currents. (f) Rate capability of NSC electrodes at increasing current densities from 0.1 to 6.4 A g<sup>-1</sup>.

The galvanostatic intermittent titration technique is used to calculate the Na<sup>+</sup> diffusion coefficient according to the following formula (S1):

$$D = \left( \frac{\Delta E_s}{\Delta E_t} \right) \frac{4L^2}{\pi\tau} \quad (\text{S1})$$

In the formula,  $\Delta E_s$  represents the change in steady-state potential of a current pulse (V),  $\Delta E_t$  is the elimination of constant current pulse potential (V) changes after iR drops,  $t$  is the duration of the current pulse,  $\tau$  is the relaxation time, and  $L$  is the diffusion length of Na<sup>+</sup>[42,57].

**Table S6.** The EIS fitting parameters of SGCS@NSC, NSC, SGCS, and GCS.

Samples	$R_s(\Omega)$	$R_{ct}(\Omega)$
SGCS@NSC	4.9	637.2
NSC	7.832	975.1
SGCS	11	1875
GCS	13.1	981